

**METHOD FOR THE PRODUCTION OF A MEMORY CELL, MEMORY  
CELL AND MEMORY CELL ARRANGEMENT**

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**Abstract**

The invention relates to a method for the production of a memory cell, a  
memory cell and a memory cell arrangement. According to the inventive method  
for the production of a memory cell, a first electrically conductive area is formed in  
10 and/or on a substrate. A second electrically conductive area is also formed at a  
given distance from the first electrically conductive area such that a cavity is  
formed between the first and second electrically conductive areas. The first and  
second electrically conductive areas are configured in such a way that when a first  
voltage is applied to the electrically conductive areas, a structure is formed from  
15 material from at least one of said electrically conductive areas, at least partially  
bridging over the distance between the electrically conductive areas. When a  
second voltage is applied to the conductive areas, the material of the structure at  
least partially bridging over the distance between the electrically conductive areas  
recedes.